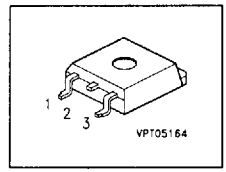
SIPMOS® Power Transistor

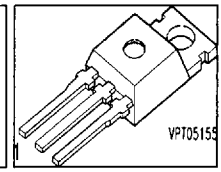
Features

- N channel
- Enhancement mode
- Avalanche rated
- d*v*/d*t* rated
- 175°C operating temperature

Product Summary

Drain source voltage	V_{DS}	55	V
Drain-Source on-state resistance	$R_{DS(on)}$	0.015	Ω
Continuous drain current	I_D	77	A





Type	Package	Ordering Code	Packaging
BUZ100S	P-TO220-3-1	Q67040-S4001-A2	Tube
BUZ100S E3045A	P-TO263-3-2	Q67040-S4001-A6	Tape and Reel
BUZ100S E3045	P-TO263-3-2	Q67040-S4001-A5	Tube

Pin 1	Pin 2	Pin 3
G	D	S

Maximum Ratings, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current T_C = 25 °C T_C = 100 °C	I_D	 77 55	A
Pulsed drain current T_C = 25 °C	I_{Dpulse}	308	
Avalanche energy, single pulse I_D = 77 A, V_{DD} = 25 V, R_{GS} = 25 Ω	E_{AS}	380	mJ
Avalanche energy, periodic limited by T_{jmax}	E_{AR}	17	
Reverse diode d*v*/d*t* I_S = 77 A, V_{DS} = 40 V, d*i*/d*t* = 200 A/µs, T_{jmax} = 175 °C	d*v*/d*t*	6	kV/µs
Gate source voltage	V_{GS}	±20	V
Power dissipation T_C = 25 °C	P_{tot}	170	W
Operating and storage temperature	T_j, T_{stg}	-55... +175	°C
IEC climatic category; DIN IEC 68-1		55/175/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	0.88	K/W
Thermal resistance, junction - ambient, leded	R_{thJA}	-	-	62	
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	62	
@ 6 cm² cooling area[F)]		-	-	40	

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain- source breakdown voltage V_{GS} = 0 V, I_D = 0.25 mA	$V_{(BR)DSS}$	55	-	-	V
Gate threshold voltage, V_{GS} = V_{DS} I_D = 130 µA	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current	I_{DSS}				µA
V_{DS} = 50 V, V_{GS} = 0 V, T_j = 25 °C		-	0.1	1	
V_{DS} = 50 V, V_{GS} = 0 V, T_j = 150 °C		-	-	100	
Gate-source leakage current V_{GS} = 20 V, V_{DS} = 0 V	I_{GSS}	-	10	100	nA
Drain-Source on-state resistance	$R_{DS(on)}$				Ω
V_{GS} = 10 , I_D = 55 A		-	0.01	0.015	

1 Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6 cm2 (one layer, 70µm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

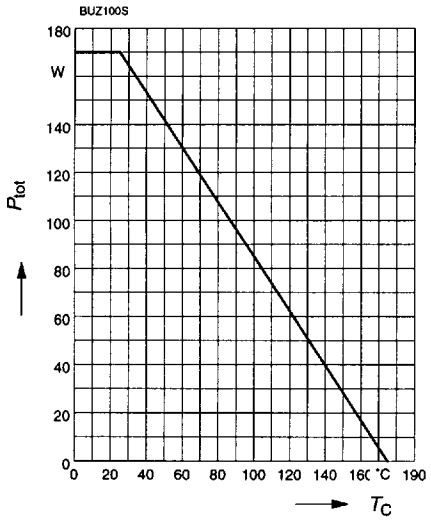
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS} \geq 2 * I_D * R_{DS(on)max}$, I_D = 55 A	g_{fs}	25	40	-	S
Input capacitance V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{iss}	-	1900	2375	pF
Output capacitance V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{oss}	-	615	770	
Reverse transfer capacitance V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{rss}	-	310	390	
Turn-on delay time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 77 A, R_G = 4.7 Ω	$t_{d(on)}$	-	15	25	ns
Rise time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 77 A, R_G = 4.7 Ω	t_r	-	30	45	
Turn-off delay time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 77 A, R_G = 4.7 Ω	$t_{d(off)}$	-	40	60	
Fall time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 77 A, R_G = 4.7 Ω	t_f	-	25	40	

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Gate to source charge V_{DD} = 40 V, I_D = 77 A	Q_{gs}	-	14	21	nC
Gate to drain charge V_{DD} = 40 V, I_D = 77 A	Q_{gd}	-	31	46.5	
Gate charge total V_{DD} = 40 V, I_D = 77 A, V_{GS} = 0 to 10 V	Q_g	-	65	100	
Gate plateau voltage V_{DD} = 40 V, I_D = 77 A	$V_{(plateau)}$	-	5.9	-	V
Reverse Diode					
Inverse diode continuous forward current T_C = 25 °C	I_S	-	-	77	A
Inverse diode direct current,pulsed T_C = 25 °C	I_{SM}	-	-	308	
Inverse diode forward voltage V_{GS} = 0 V, I_F = 154 A	V_{SD}	-	1.25	1.8	V
Reverse recovery time V_R = 30 V, I_F=I_S , di_F/dt = 100 A/µs	t_{rr}	-	105	160	ns
Reverse recovery charge V_R = 30 V, I_F=I_S , di_F/dt = 100 A/µs	Q_{rr}	-	0.16	0.25	µC

Power Dissipation

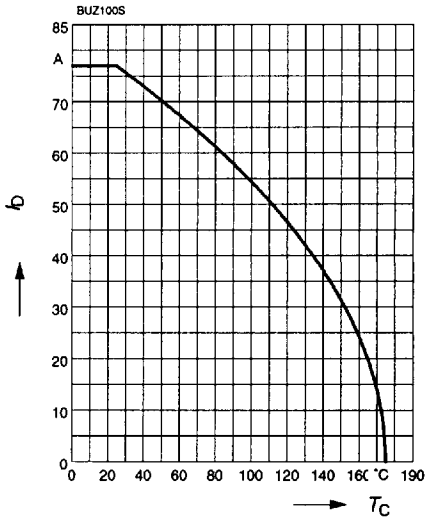
$P_{tot} = f(T_C)$



Drain current

$I_D = f(T_C)$

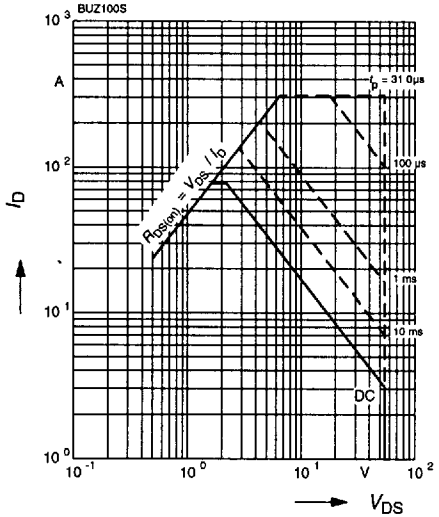
parameter: $V_{GS} \geq 10$ V



Safe operating area

$I_D = f(V_{DS})$

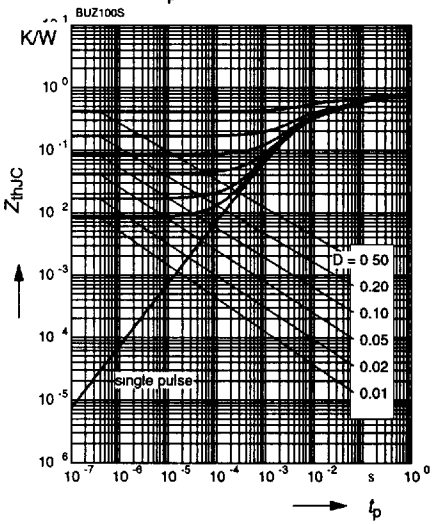
parameter : $D = 0$, $T_C = 25$ °C



Transient thermal impedance

$Z_{thJC} = f(t_p)$

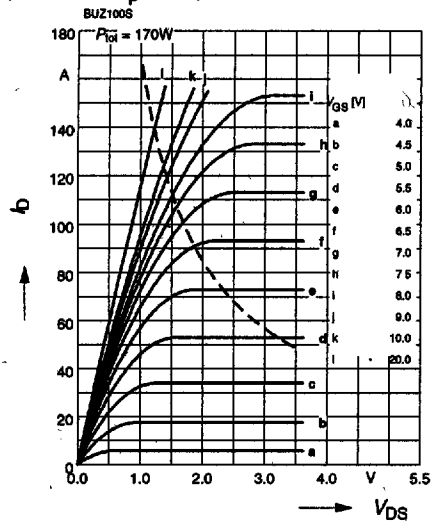
parameter : $D = t_p/T$



Typ. output characteristics

$I_D = f(V_{DS})$

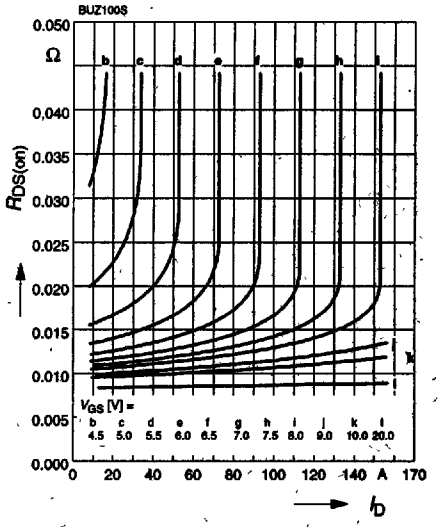
parameter: t_p = 80 µs



Typ. drain-source-on-resistance

$R_{DS(on)} = f(I_D)$

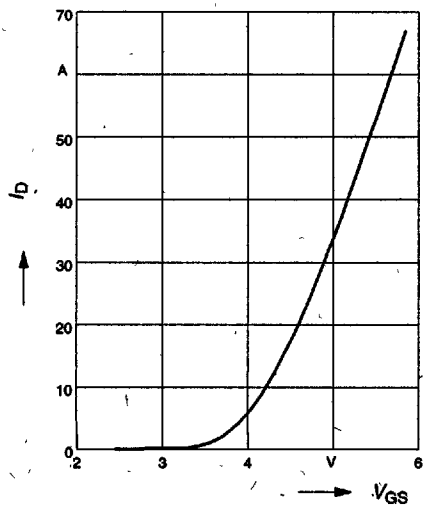
parameter: V_{GS}



Typ. transfer characteristics $I_D = f(V_{GS})$

parameter: t_p = 80 µs

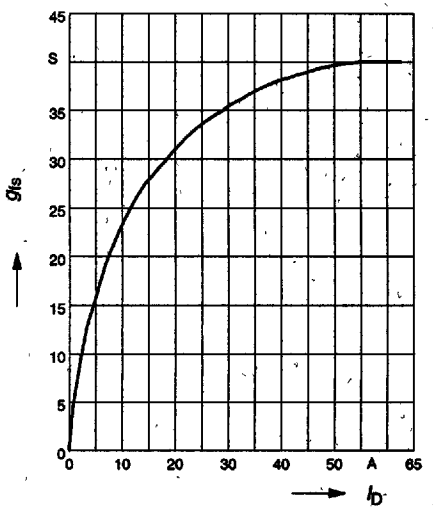
$V_{DS} \geq 2 \times I_D \times R_{DS(on)\,max}$



Typ. forward transconductance

$g_{fs} = f(I_D)$; T_j = 25°C

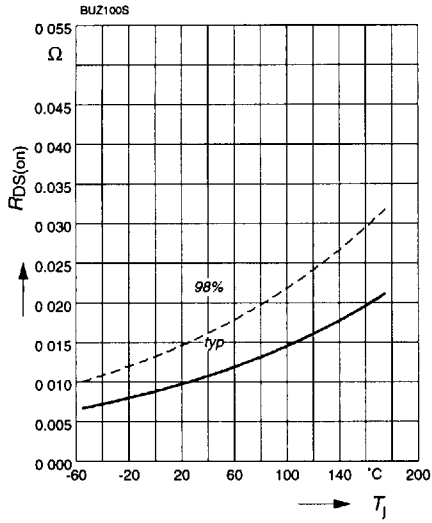
parameter: g_{fs}



Drain-source on-resistance

$R_{DS(on)} = f(T_j)$

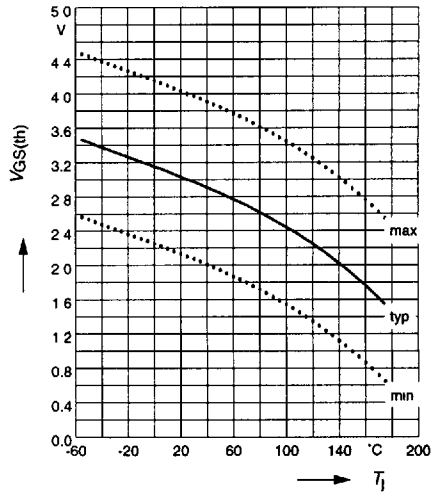
parameter : I_D = 55 A, V_{GS} = 10



Gate threshold voltage

$V_{GS(th)} = f(T_j)$

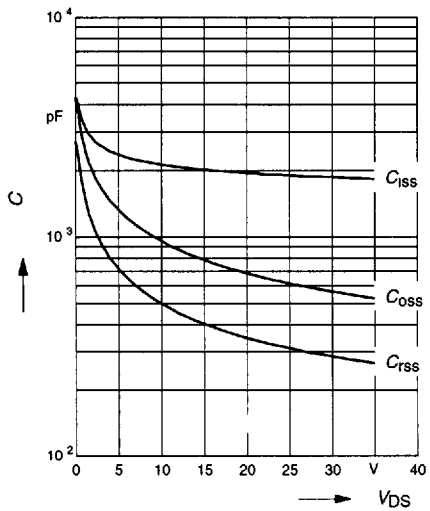
parameter : $V_{GS} = V_{DS}$, I_D = 130 µA



Typ. capacitances

$C = f(V_{DS})$

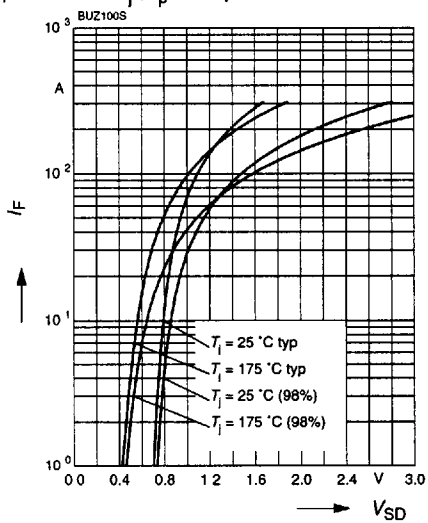
parameter: V_{GS} = 0 V, f = 1 MHz



Forward characteristics of reverse diode

$I_F = f(V_{SD})$

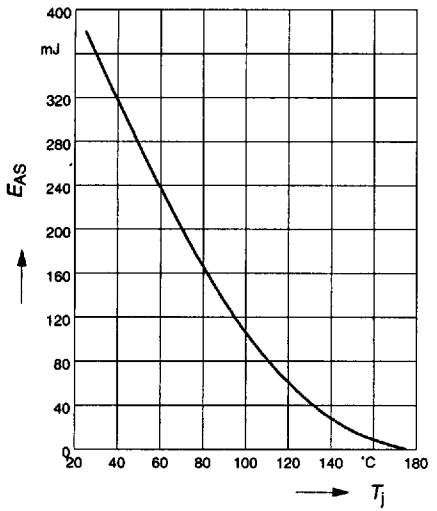
parameter: T_j , t_p = 80 µs



Avalanche Energy $E_{AS} = f(T_j)$

parameter: $I_D = 77$ A, $V_{DD} = 25$ V

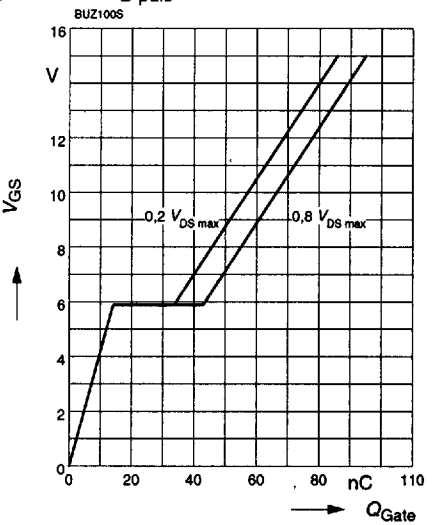
$R_{GS} = 25\ \Omega$



Typ. gate charge

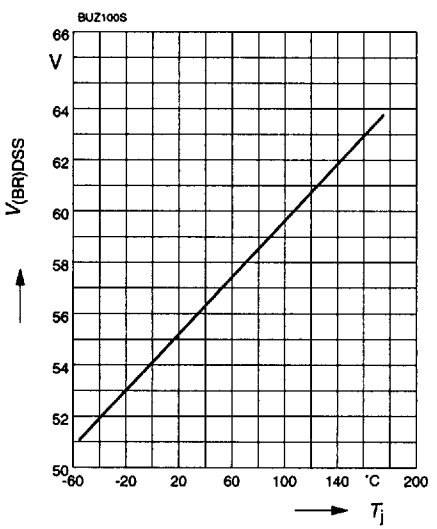
$V_{GS} = f(Q_{Gate})$

parameter: $I_{D\ puls} = 77$ A



Drain-source breakdown voltage

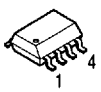
$V_{(BR)DSS} = f(T_j)$

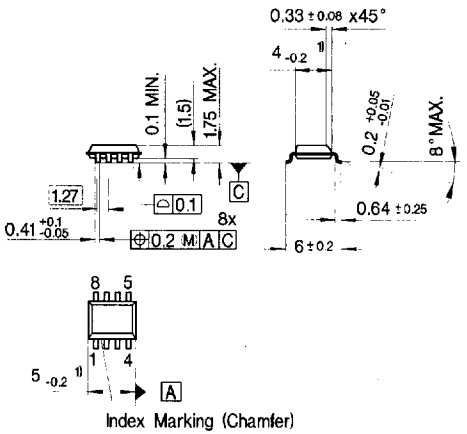


Gehäusemaßbilder
(Maße in mm, wenn nicht anders angegeben)

Package Outlines
(Dimensions in mm, unless otherwise specified)

P-DSO-8-6/-7
Gewicht etwa 0.15 g
Approx. weight 0.15 g

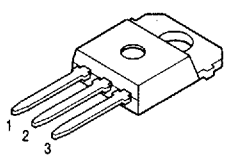


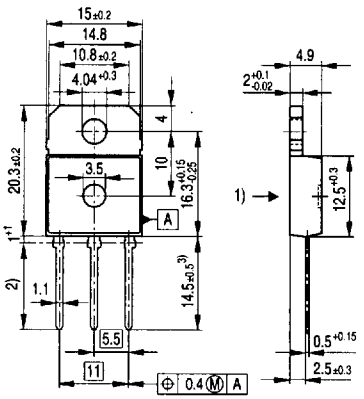


1) Does not include plastic or metal protrusion of 0.15 max. per side

Bild 16 **Figure 16**

P-TO218-AA (P-TO218-2-1)
Gewicht etwa 4.9 g
Approx. weight 4.9 g



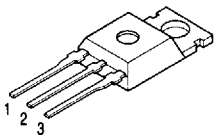


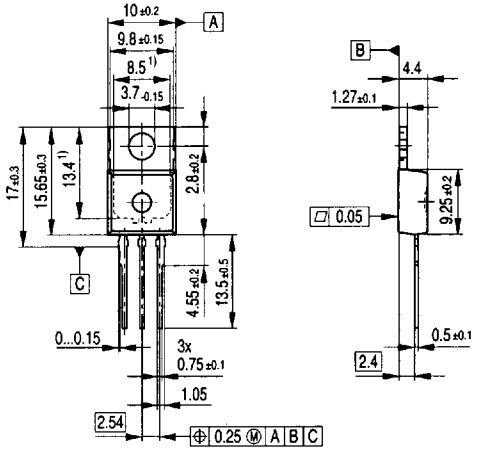
1) Punch direction, burr max. 0.04
2) Dip tinning
3) Max. 15.5 by dip tinning
press burr max. 0.05
radii not dimensioned max. 0.2

GPT05156

Bild 17 **Figure 17**

P-TO220-3-1
Gewicht etwa 1.8 g
Approx. weight 1.8 g

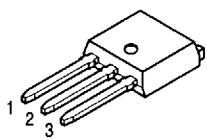


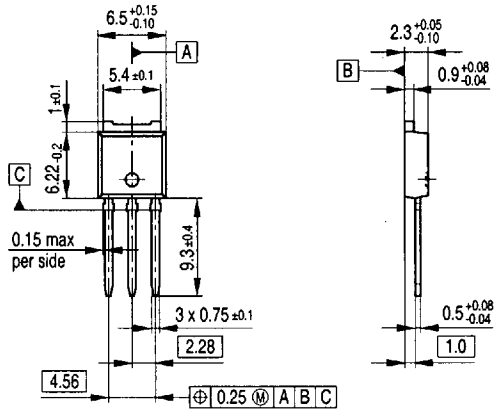


1) Typical
All metal surfaces tin plated, except area of cut. GPT05155

Bild 18 **Figure 18**

P-TO251-3-1
Gewicht etwa 2.0 g
Approx. weight 2.0 g

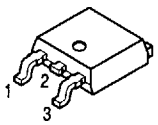


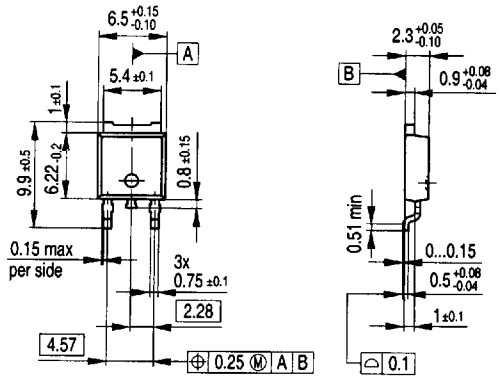


All metal surfaces tin plated, except area of cut. GPT09050

Bild 19 **Figure 19**

P-TO252-3-1
Gewicht etwa 0.38 g
Approx. weight 0.38 g



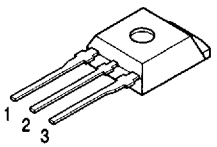


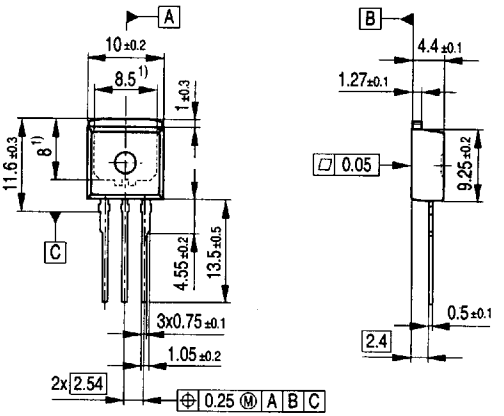
All metal surfaces tin plated, except area of cut.

GPT09051

Bild 20 **Figure 20**

P-TO262-3-1/I²PAK



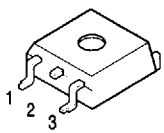


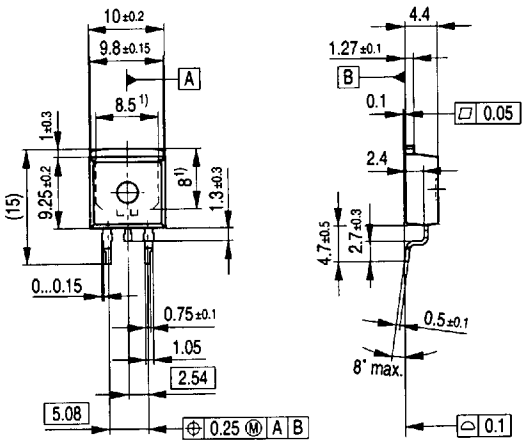
1) Typical
Metal surface min. X = 7.25, Y = 7.35
All metal surfaces tin plated, except area of cut.

GPT09244

Bild 21 **Figure 21**

P-TO263-3-2/D²PAK
Gewicht etwa 1.38 g
Approx. weight 1.38 g



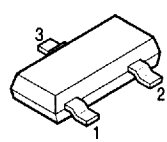


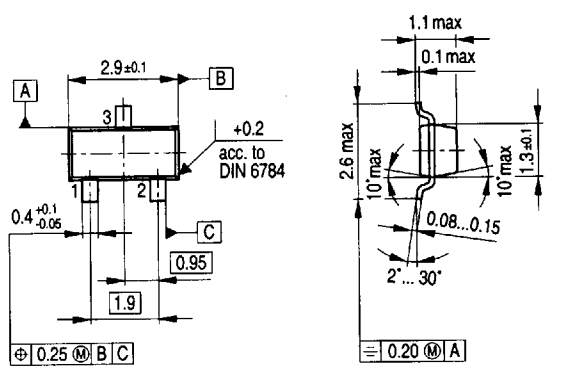
1) Typical
All metal surfaces tin plated, except area of cut.

GPT09085

Bild 22 **Figure 22**

SOT-23 (P-SOT23-3-1)
Gewicht etwa 0.01 g
Approx. weight 0.01 g

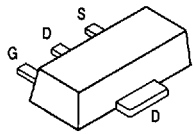




GPS05557

Bild 23 **Figure 23**

SOT-89
Gewicht etwa 0.01 g
Approx. weight 0.01 g



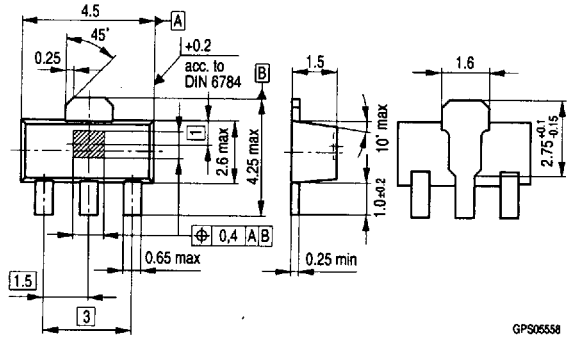
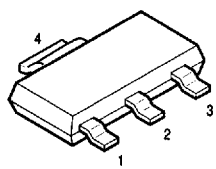


Bild 24 **Figure 24**

SOT-223 (P-SOT223-4-1)
Gewicht etwa 0.15 g
Approx. weight 0.15 g



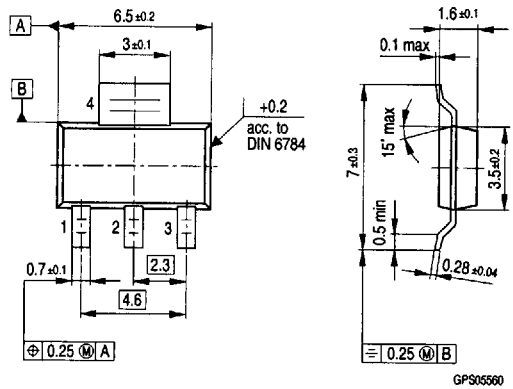
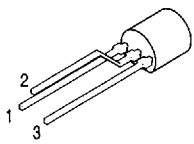


Bild 25 **Figure 25**

TO-92
Gewicht etwa 0.23 g
Approx. weight 0.23 g



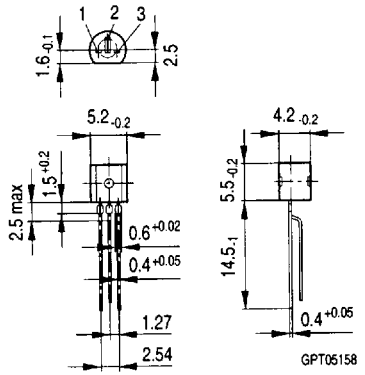
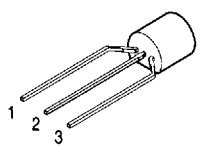


Bild 26 **Figure 26**

TO-92-E6288
Gewicht etwa 0.23 g
Approx. weight 0.23 g



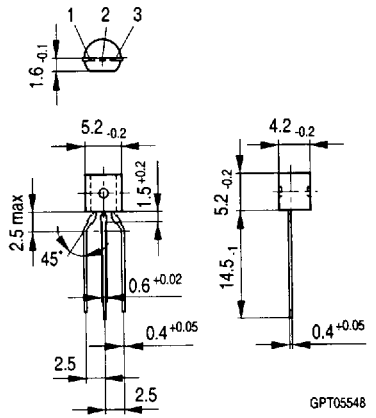


Bild 27 **Figure 27**

Sorts of Packing
Package outlines for tubes, trays etc. are contained in our Data Book "Package Information".

SMD = Surface Mounted Device